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Total Number of Pages in This Submission	Allomey Docker Number	MI22-2295				
Fee Transmittal Form  Fee Attached  Amendment/Reply  After Final  Affidavits/declaration(s)  Extension of Time Request  Express Abandonment Request  Information Disclosure Statement  Certified Copy of Priority  Document(s)	Drawing(s)  Licensing-related Papers  Petition  Petition to Convert to a Provisional Application Power of Attorney, Revocation Change of Correspondence Addre Terminal Disclaimer  Request for Refund  CD, Number of CD(s)	After Allowance Communication to a Technology Center (TC)  Appeal Communication to Board of Appeals and Interferences  Appeal Communication to TC (Appeal Notice, Brief, Reply Brief)  Proprietary Information				
Response to Missing Parts/ Incomplete Application  Response to Missing Parts under 37 CFR 1.52 or 1.53	Response to Missing Parts/ Incomplete Application Response to Missing Parts  EV550717282					
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Pirm or Wells St. John, P.S.  Individual Signature  Date CERTIFICATE OF TRANSMISSION/MAILING  I hereby certify that this correspondence is being facsimile transmitted to the USPTO or deposited with the United States Postal Service with sufficient postage as mail in an envelope addressed to: Commissioner for Patents, Washington, DC 20231 on this date:						
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This collection of information is required by 37 CFR 1.5. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

atent Application Serial No	
Filing Date	December 10, 2003
Inventor	H. Montgomery Manning et al.
Assignee	Micron Technology, Inc.
Group Art Unit	2812
Examiner	Unknown
Attorney Docket No	MI22-2295
Customer No	021567
Title: Semiconductor Constructions, and	Methods of Forming Capacitor Devices

## SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

EV 550717282

This Supplemental Information Disclosure Statement is being filed within three months of the filing date of the application or before the mailing of a first Office Action on the merits, whichever occurs last. Therefore, no fee is believed to be required. However, in the event that a fee is required for filing this Supplemental Information Disclosure Statement, please charge the fee specified under 37 C.F.R. § 1.17(p) to Deposit Account No. 23-0925.

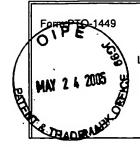
Respectfully submitted,

Dated:

David G. Latwesen, Ph.D.

Reg. No. 38,533

By:



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ATTY. DOCKET NO. MI22-2295

SERIAL NO. 10/733,181

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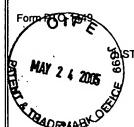
**FILING DATE** December 10, 2003

**GROUP** 2812

Examiner's Initials		Document Number	Date	Name	(	Class Subo		Date ropriate
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	AB			EV55071	-			
	AC							
FOREIGN	PATENT	T DOCUMENTS						
		Document Number	Date	Country	Class	Subclass	Transla	tion
		Number					Yes	No
	AD	DE 4447804	1/2002	Germany			Abstract	
	AE							
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609, Draw line through citation if not in conformance and not

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